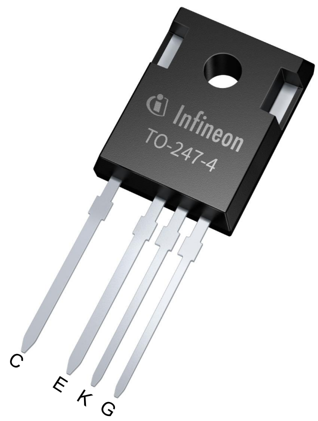
Short circuit rugged 1200 V TRENCHSTOP™ IGBT 7 technology copacked with soft, fast recovery Emitter Controlled 7 diode



Features

- V_{CE} = 1200 V
- I_C = 40 A
- IGBT co-packed with full current, soft and low Qrr diode
- Low saturation voltage V_{CEsat} = 2.0 V at T_{vj} = 175°C
- Optimized for hard switching topologies (2-L inverter, 3-L NPC T-type, ...)
- Short circuit ruggedness 8 µs
- Wide range of dv/dt controllability
- Complete product spectrum and PSpice Models: http://www.infineon.com/igbt/

Potential applications

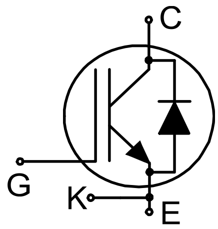
- Industrial drives
- Industrial power supplies
- Solar inverters

Product validation

- Qualified for industrial applications according to the relevant tests of JEDEC47/20/22

Halogen-free
Lead-free
Green
RoHS

Description



Type	Package	Marking
IKZA40N120CS7	PG-TO247-4-STD-NT3.7	K40MCS7

Table of contents

1 Package

Table 1 Characteristic values

Parameter	Symbol	Note or test condition	Values			Unit
			Min.	Typ.	Max.	
Internal emitter inductance measured 5 mm (0.197 in.) from case	L_E			13		nH
Storage temperature	T_{stg}		-55		150	°C
Soldering temperature	T_{sold}	wave soldering 1.6 mm (0.063 in.) from case for 10 s			260	°C
Mounting torque	M	M3 screw, Maximum of mounting process: 3			0.6	Nm
Thermal resistance, junction-ambient	$R_{th(j\text{-}a)}$				40	K/W
IGBT thermal resistance, junction-case	$R_{th(j\text{-}c)}$			0.3	0.42	K/W
Diode thermal resistance, junction-case	$R_{th(j\text{-}c)}$			0.55	0.75	K/W

2 IGBT

Table 2 Maximum rated values

Parameter	Symbol	Note or test condition		Values	Unit
Collector-emitter voltage	V_{CE}	$T_{vj} \geq 25$ °C		1200	V
DC collector current, limited by T_{vjmax}	I_C		$T_c = 25$ °C	82	A
			$T_c = 100$ °C	56	
Pulsed collector current, t_p limited by T_{vjmax}	I_{Cpulse}			120	A
Turn-off safe operating area		$V_{CE} \leq 1200$ V, $T_{vj} \leq 175$ °C		120	A
Gate-emitter voltage	V_{GE}			±20	V
Transient gate-emitter voltage	V_{GE}	$t_p \leq 0.5$ µs, $D < 0.001$		±25	V
Short-circuit withstand time	t_{SC}	$V_{CC} \leq 600$ V, $V_{GE} = 15$ V, Allowed number of short circuits < 1000, Time between short circuits ≥ 1.0 s, $T_{vj} = 150$ °C		8	µs
Power dissipation	P_{tot}	$T_{vj} \leq 175$ °C	$T_c = 25$ °C	357	W
			$T_c = 100$ °C	179	

Table 3 Characteristic values

Parameter	Symbol	Note or test condition		Values			Unit
				Min.	Typ.	Max.	
Collector-emitter saturation voltage	V_{CEsat}	I_C = 40 A, V_{GE} = 15 V	T_{vj} = 25 °C		1.65	2	V
			T_{vj} = 175 °C		2		
Gate-emitter threshold voltage	V_{GEth}	I_C = 0.78 mA, V_{CE} = V_{GE}		5.1	5.7	6.5	V
Zero gate-voltage collector current	I_{CES}	V_{CE} = 1200 V, V_{GE} = 0 V	T_{vj} = 25 °C			40	µA
			T_{vj} = 175 °C		3500		
Gate-emitter leakage current	I_{GES}	V_{CE} = 0 V, V_{GE} = 20 V				100	nA
Transconductance	g_{fs}	I_C = 40 A, V_{CE} = 20 V, T_{vj} = 175 °C			17		S
Short-circuit collector current	I_{SC}	V_{CC} ≤ 600 V, V_{GE} = 15 V, t_{SC} ≤ 8 µs, Allowed number of short circuits < 1000, Time between short circuits ≥ 1.0 s, T_{vj} = 150 °C			240		A
Input capacitance	C_{ies}	V_{CE} = 25 V, V_{GE} = 0 V, f = 100 kHz			5.5		nF
Output capacitance	C_{oes}	V_{CE} = 25 V, V_{GE} = 0 V, f = 100 kHz			120		pF
Reverse transfer capacitance	C_{res}	V_{CE} = 25 V, V_{GE} = 0 V, f = 100 kHz			27		pF
Gate charge	Q_G	I_C = 40 A, V_{GE} = 15 V, V_{CC} = 960 V			230		nC
Turn-on delay time	$t_{d(on)}$	V_{CC} = 600 V, V_{GE} = 0/15 V, $R_{G(on)}$ = 4 Ω, $R_{G(off)}$ = 4 Ω	T_{vj} = 25 °C, I_C = 40 A		28		ns
			T_{vj} = 175 °C, I_C = 40 A		29		
Rise time (inductive load)	t_r	V_{CC} = 600 V, V_{GE} = 0/15 V, $R_{G(on)}$ = 4 Ω, $R_{G(off)}$ = 4 Ω	T_{vj} = 25 °C, I_C = 40 A		15		ns
			T_{vj} = 175 °C, I_C = 40 A		19		
Turn-off delay time	$t_{d(off)}$	V_{CC} = 600 V, V_{GE} = 0/15 V, $R_{G(on)}$ = 4 Ω, $R_{G(off)}$ = 4 Ω	T_{vj} = 25 °C, I_C = 40 A		176		ns
			T_{vj} = 175 °C, I_C = 40 A		258		
Fall time (inductive load)	t_f	V_{CC} = 600 V, V_{GE} = 0/15 V, $R_{G(on)}$ = 4 Ω, $R_{G(off)}$ = 4 Ω	T_{vj} = 25 °C, I_C = 40 A		110		ns
			T_{vj} = 175 °C, I_C = 40 A		260		
Turn-on energy	E_{on}	V_{CC} = 600 V, V_{GE} = 0/15 V, $R_{G(on)}$ = 4 Ω, $R_{G(off)}$ = 4 Ω	T_{vj} = 25 °C, I_C = 40 A		1.23		mJ
			T_{vj} = 175 °C, I_C = 40 A		2.1		

(table continues...)

Table 3 (continued) Characteristic values

Parameter	Symbol	Note or test condition		Values			Unit
				Min.	Typ.	Max.	
Turn-off energy	E_{off}	V_{CC} = 600 V, V_{GE} = 0/15 V, $R_{G(on)}$ = 4 Ω, $R_{G(off)}$ = 4 Ω	T_{vj} = 25 °C, I_C = 40 A		1.78		mJ
Total switching energy	E_{ts}	V_{CC} = 600 V, V_{GE} = 0/15 V, $R_{G(on)}$ = 4 Ω, $R_{G(off)}$ = 4 Ω	T_{vj} = 25 °C, I_C = 40 A		3.01		mJ
			T_{vj} = 175 °C, I_C = 40 A		5.8		
Operating junction temperature	T_{vj}			-40		175	°C

Note: Electrical Characteristic, at T_{vj} = 25°C, unless otherwise specified.

3 Diode

Table 4 Maximum rated values

Parameter	Symbol	Note or test condition		Values	Unit
Diode forward current, limited by T_{vjmax}	I_F		T_c = 25 °C	69	A
			T_c = 100 °C	46	
Diode pulsed current, t_p limited by T_{vjmax}	I_{Fpulse}			120	A
Power dissipation	P_{tot}		T_c = 25 °C	208	W
			T_c = 100 °C	104	

Table 5 Characteristic values

Parameter	Symbol	Note or test condition		Values			Unit
				Min.	Typ.	Max.	
Diode forward voltage	V_F	I_F = 40 A	T_{vj} = 25 °C		1.65	2.15	V
			T_{vj} = 175 °C		1.6		
Diode reverse recovery time	t_{rr}	V_R = 600 V, $R_{G(on)}$ = 4 Ω	T_{vj} = 25 °C, I_F = 40 A		110		ns
			T_{vj} = 175 °C, I_F = 40 A		220		
Diode reverse recovery charge	Q_{rr}	V_R = 600 V, $R_{G(on)}$ = 4 Ω	T_{vj} = 25 °C, I_F = 40 A		2.5		µC
			T_{vj} = 175 °C, I_F = 40 A		6.3		

(table continues...)

Table 5 (continued) Characteristic values

Parameter	Symbol	Note or test condition		Values			Unit
				Min.	Typ.	Max.	
Diode peak reverse recovery current	I_{rrm}	V_R = 600 V, $R_{G(on)}$ = 4 Ω	T_{vj} = 25 °C, I_F = 40 A		63		A
			T_{vj} = 175 °C, I_F = 40 A		88		
Diode peak rate of fall of reverse recovery current	di_{rr}/dt	V_R = 600 V, $R_{G(on)}$ = 4 Ω	T_{vj} = 25 °C, I_F = 40 A		-1020		A/µs
			T_{vj} = 175 °C, I_F = 40 A		-1430		
Reverse recovery energy	E_{rec}	V_R = 600 V, $R_{G(on)}$ = 4 Ω	T_{vj} = 25 °C, I_F = 40 A		0.89		mJ
			T_{vj} = 175 °C, I_F = 40 A		2.54		
Operating junction temperature	T_{vj}			-40		175	°C

Note: *For optimum lifetime and reliability, Infineon recommends operating conditions that do not exceed 80% of the maximum ratings stated in this datasheet.*

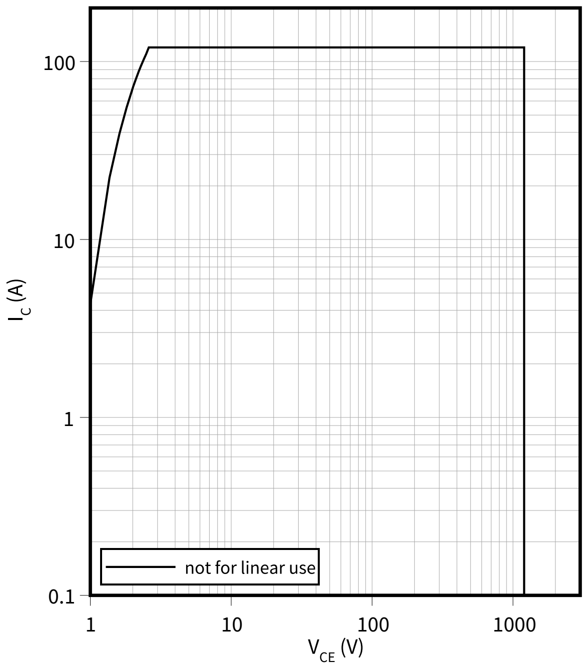
Dynamic test circuit, parasitic inductance L_σ = 30 nH, C_σ = 18 pF.

4 Characteristics diagrams

Reverse bias safe operating area

$I_C = f(V_{CE})$

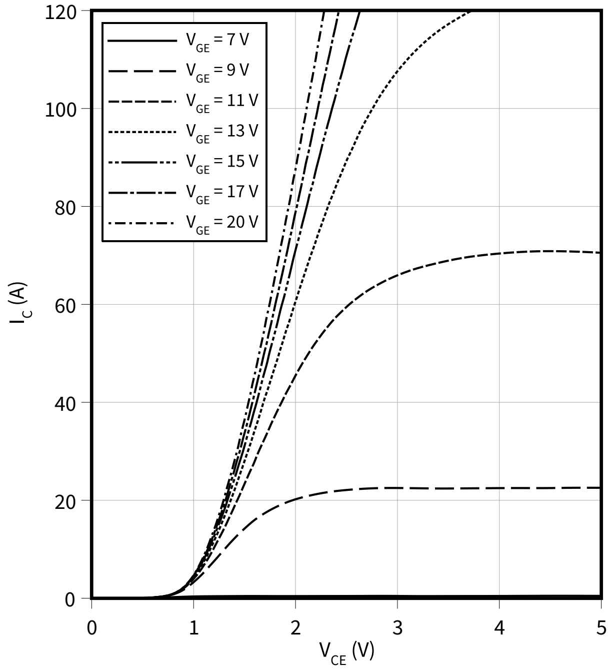
$T_{vj} \leq 175\ °C$, $V_{CE} \leq 1200\ V$



Typical output characteristic

$I_C = f(V_{CE})$

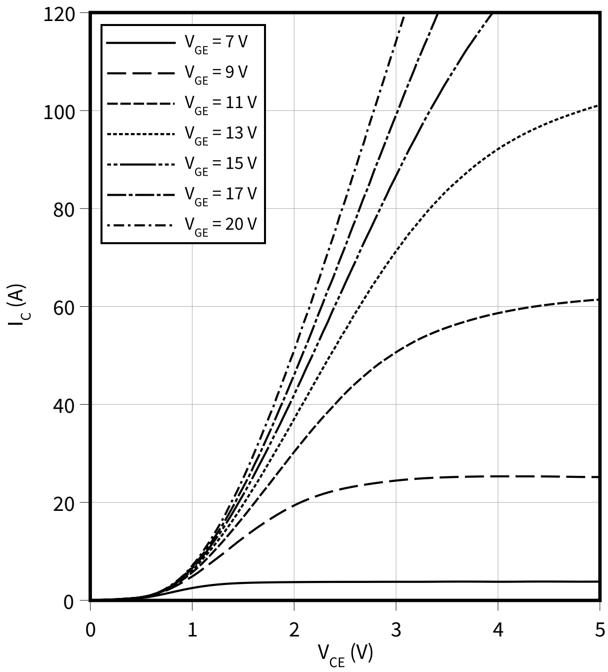
$T_{vj} = 25\ °C$



Typical output characteristic

$I_C = f(V_{CE})$

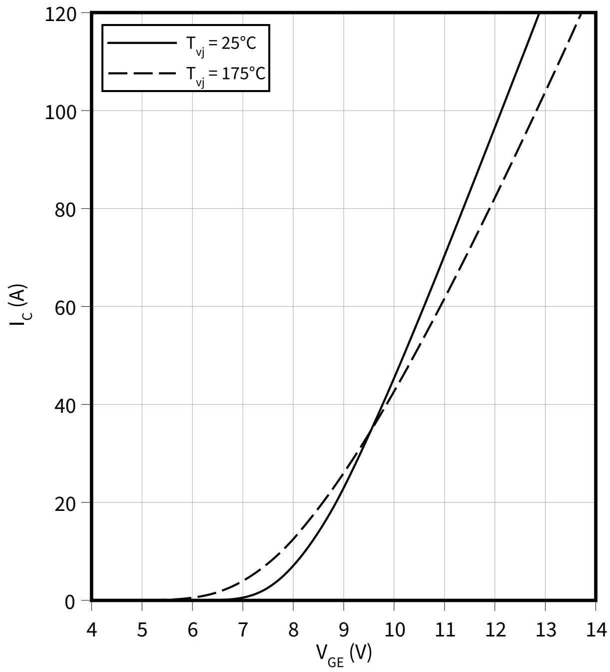
$T_{vj} = 175\ °C$



Typical transfer characteristic

$I_C = f(V_{GE})$

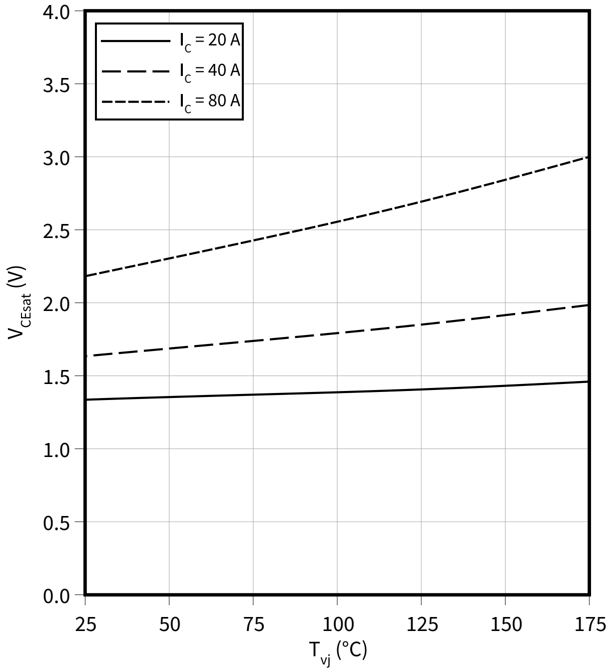
$V_{CE} = 20\ V$



Typical collector-emitter saturation voltage as a function of junction temperature

$V_{CEsat} = f(T_{vj})$

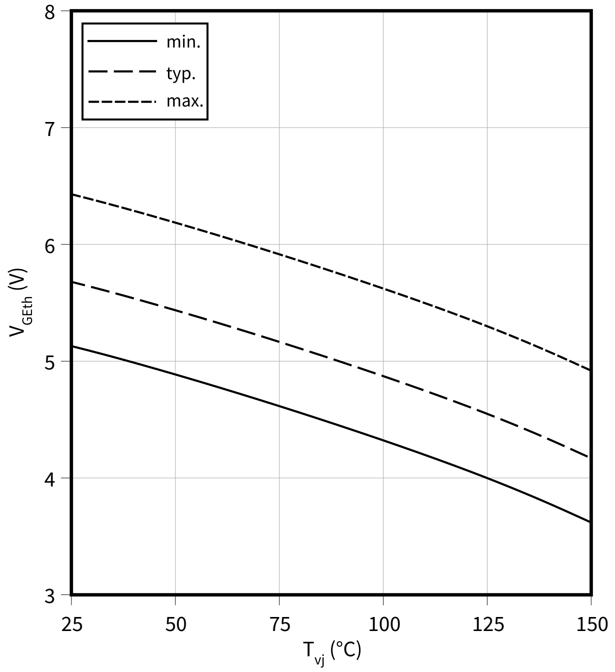
$V_{GE} = 15$ V



Gate-emitter threshold voltage as a function of junction temperature

$V_{GEth} = f(T_{vj})$

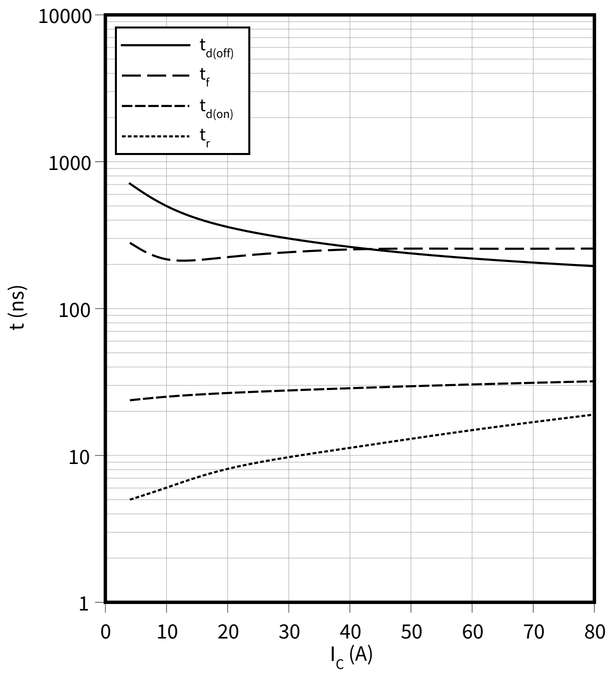
$I_C = 0.78$ mA



Typical switching times as a function of collector current

$t = f(I_C)$

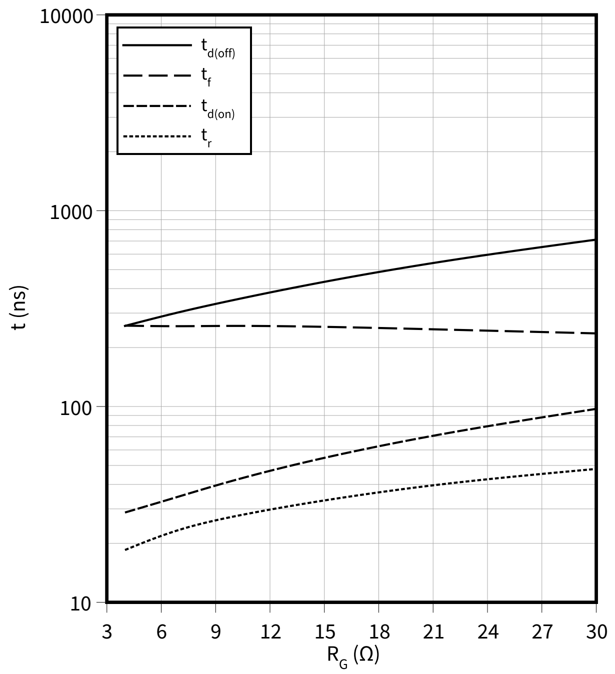
$V_{CC} = 600$ V, $T_{vj} = 175$ °C, $V_{GE} = 0/15$ V, $R_G = 4\ \Omega$



Typical switching times as a function of gate resistor

$t = f(R_G)$

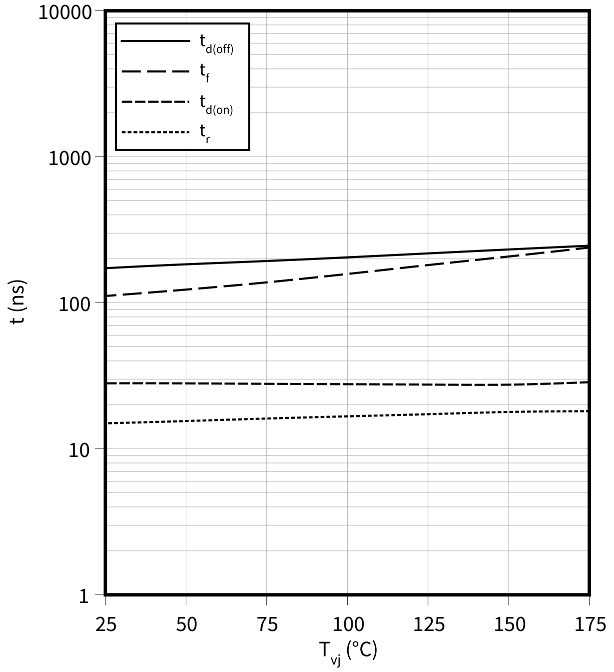
$I_C = 40$ A, $V_{CC} = 600$ V, $T_{vj} = 175$ °C, $V_{GE} = 0/15$ V



Typical switching times as a function of junction temperature

$t = f(T_{vj})$

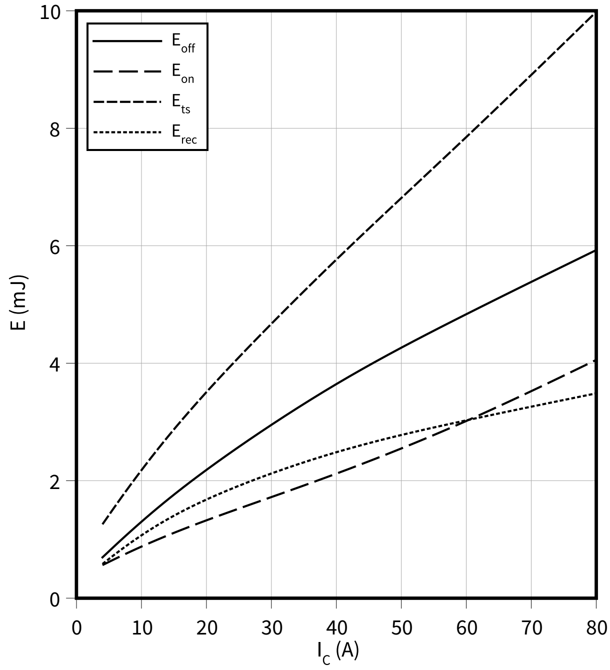
I_C = 40 A, V_{CC} = 600 V, V_{GE} = 0/15 V, R_G = 4 Ω



Typical switching energy losses as a function of collector current

$E = f(I_C)$

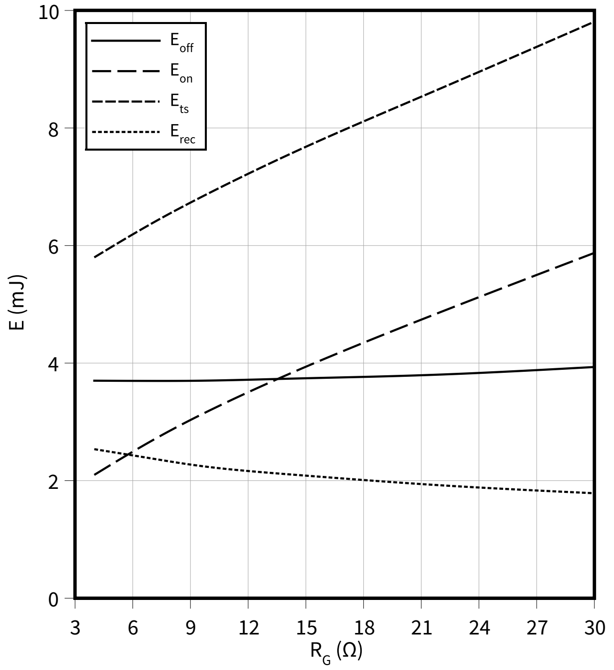
V_{CC} = 600 V, T_{vj} = 175 °C, V_{GE} = 0/15 V, R_G = 4 Ω



Typical switching energy losses as a function of gate resistor

$E = f(R_G)$

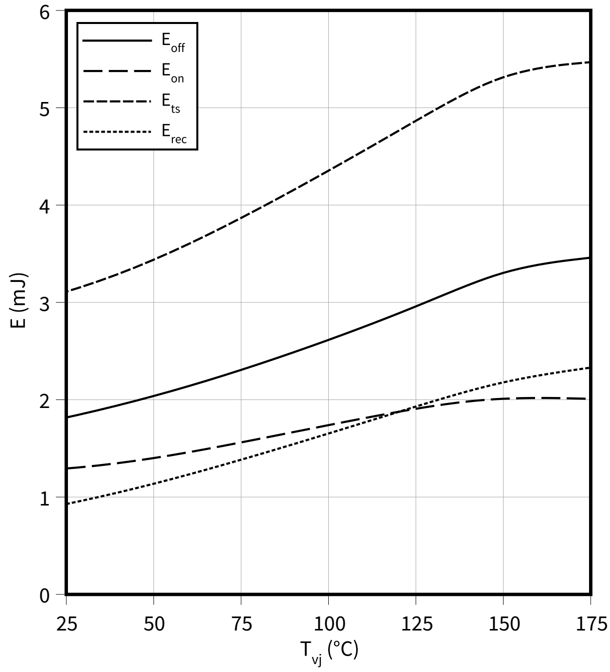
I_C = 40 A, V_{CC} = 600 V, T_{vj} = 175 °C, V_{GE} = 0/15 V



Typical switching energy losses as a function of junction temperature

$E = f(T_{vj})$

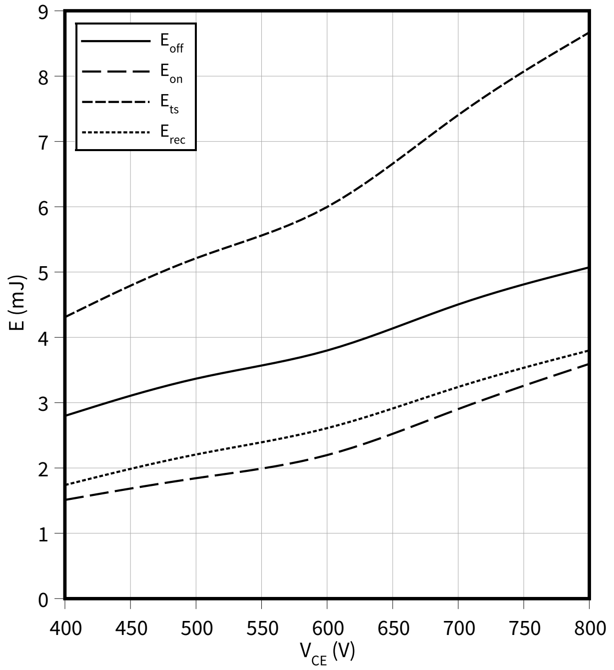
I_C = 40 A, V_{CC} = 600 V, V_{GE} = 0/15 V, R_G = 4 Ω



Typical switching energy losses as a function of collector emitter voltage

$E = f(V_{CE})$

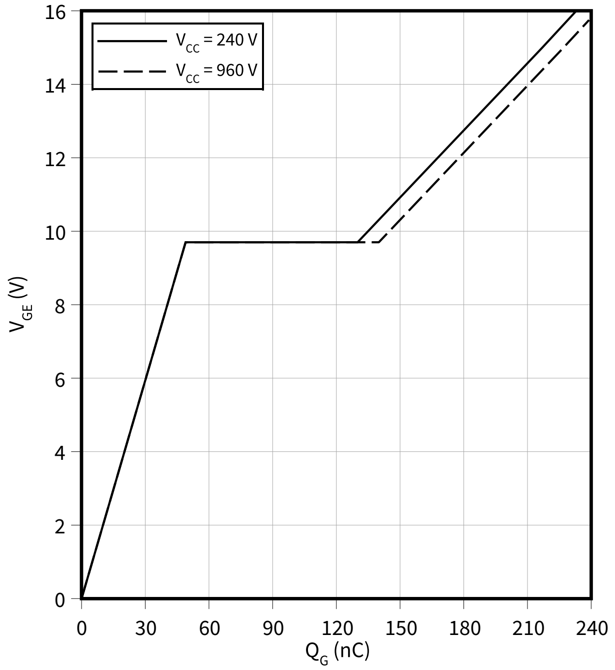
$I_C = 40$ A, $V_{GE} = 0/15$ V, $T_{vj} = 175$ °C, $R_G = 4\ \Omega$



Typical gate charge

$V_{GE} = f(Q_G)$

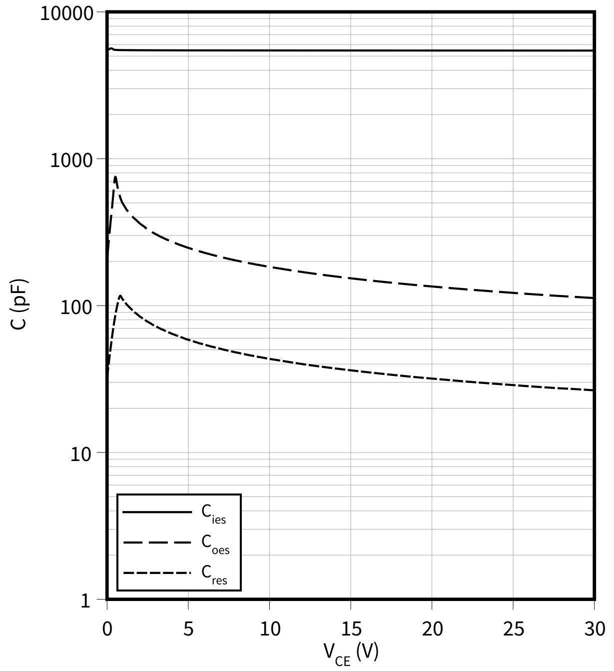
$I_C = 40$ A



Typical capacitance as a function of collector-emitter voltage

$C = f(V_{CE})$

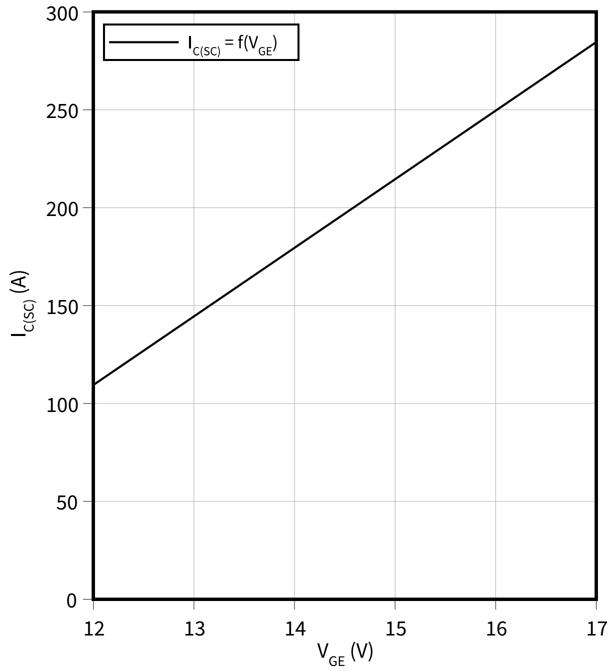
$f = 100$ kHz, $V_{GE} = 0$ V



Typical short circuit collector current as a function of gate-emitter voltage

$I_{C(SC)} = f(V_{GE})$

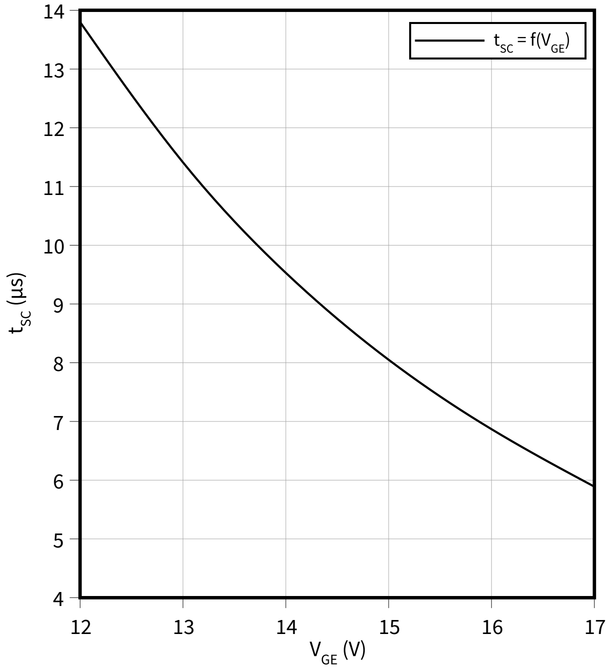
$T_{vj} = 150$ °C, $V_{CC} \leq 600$ V



Short circuit withstand time as a function of gate-emitter voltage

$t_{SC} = f(V_{GE})$

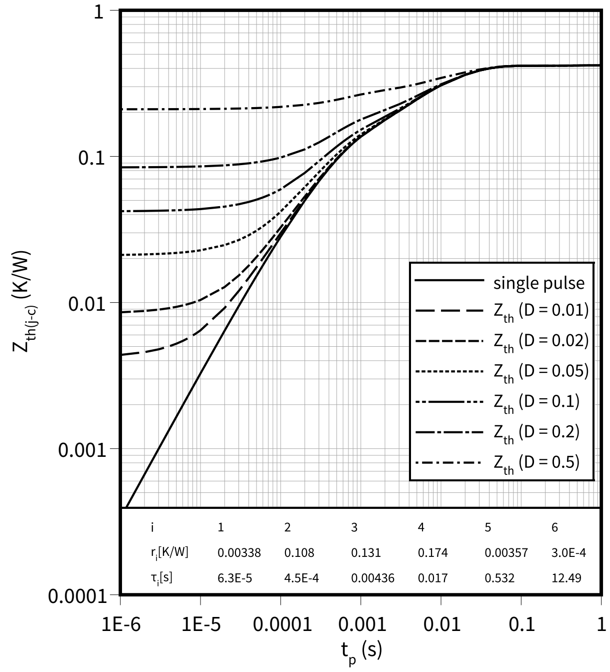
$T_{vj} \leq 150$ °C, $V_{CC} \leq 600$ V



IGBT transient thermal impedance as a function of pulse width

$Z_{th(j-c)} = f(t_p)$

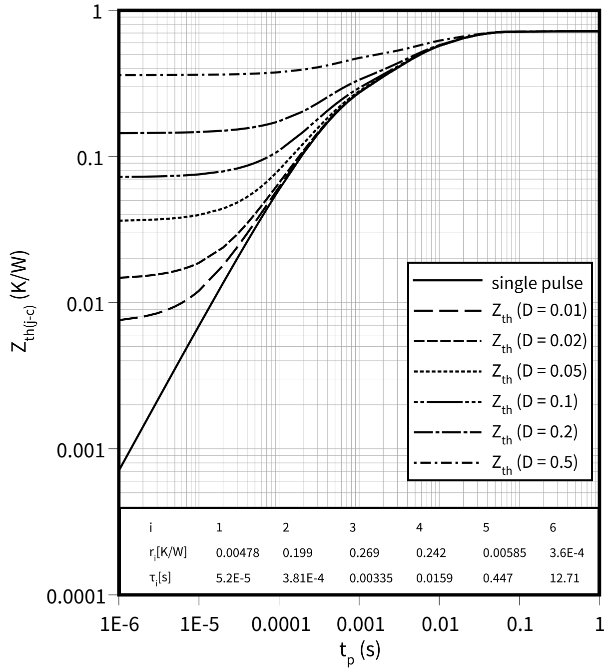
$D = t_p/T$



Diode transient thermal impedance as a function of pulse width

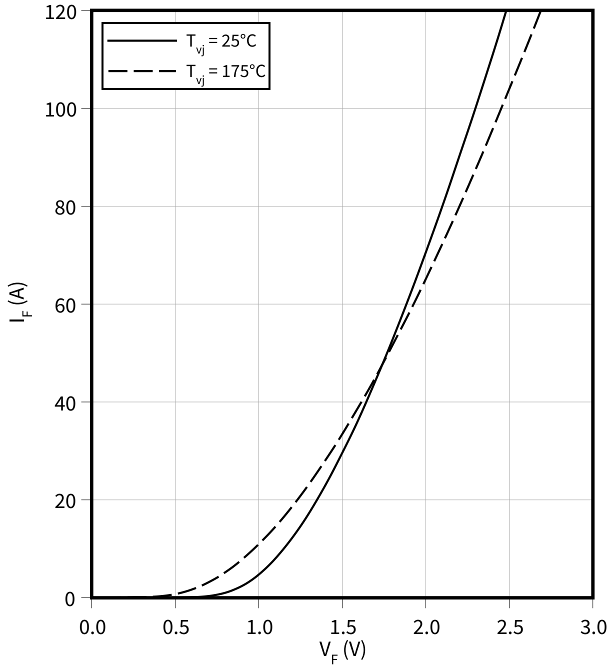
$Z_{th(j-c)} = f(t_p)$

$D = t_p/T$

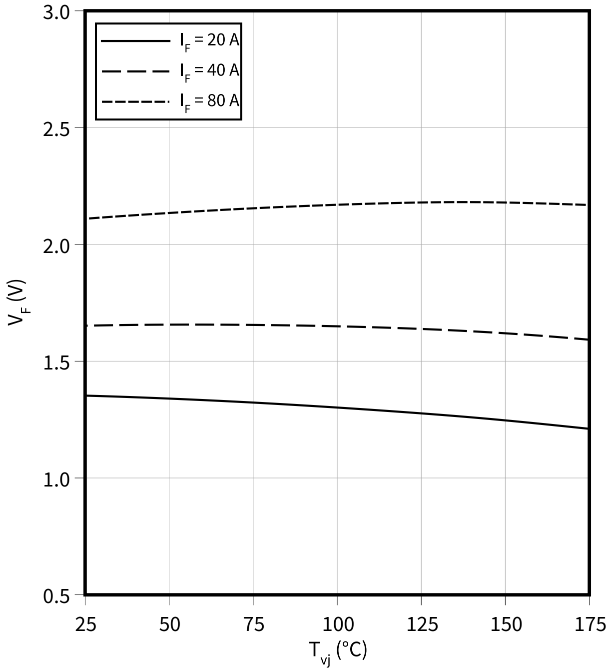


Typical diode forward current as a function of forward voltage

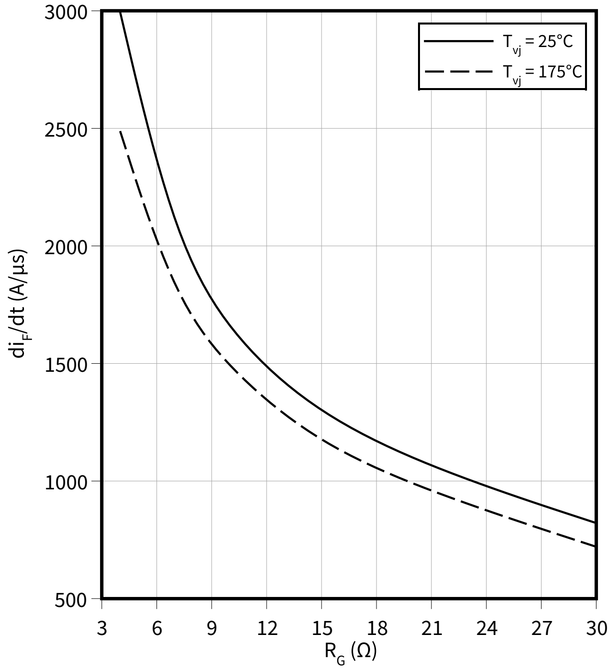
$I_F = f(V_F)$



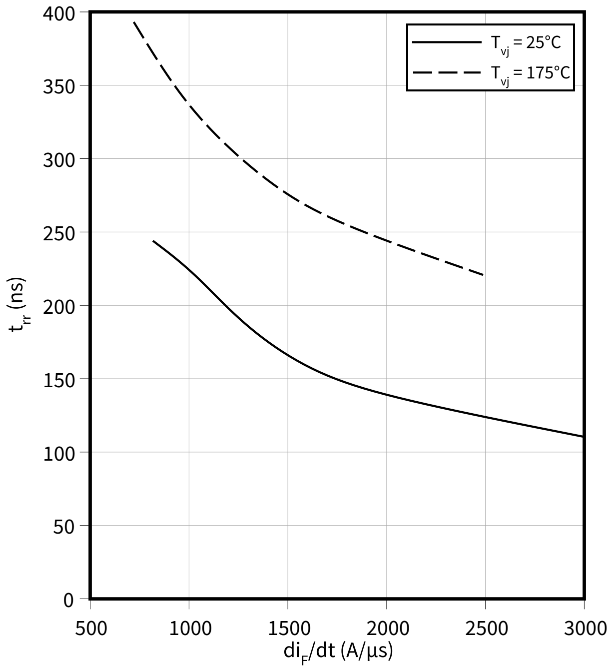
Typical diode forward voltage as a function of junction temperature
$V_F = f(T_{vj})$



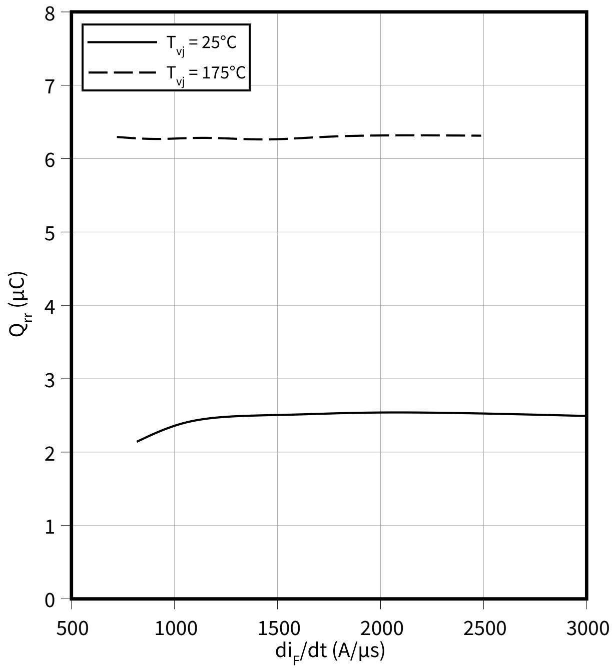
Typical diode current slope as a function of gate resistor
$di_F/dt = f(R_G)$
$V_R = 600$ V, $I_F = 40$ A



Typical reverse recovery time as a function of diode current slope
$t_{rr} = f(di_F/dt)$
$V_R = 600$ V, $I_F = 40$ A



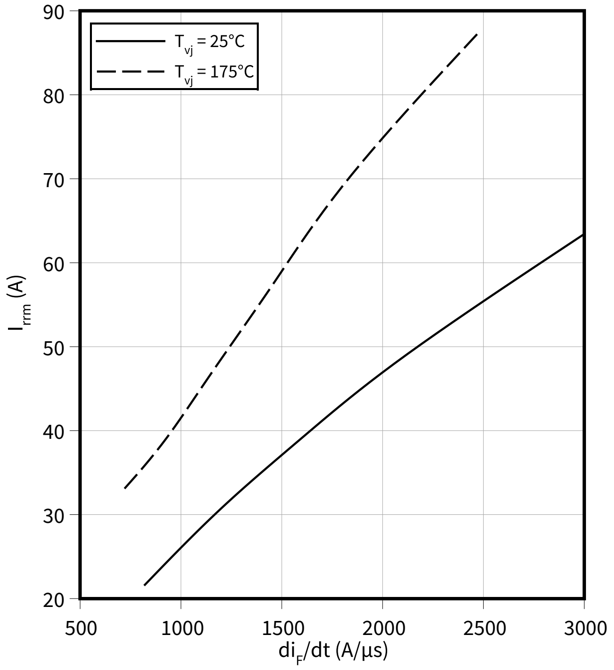
Typical reverse recovery charge as a function of diode current slope
$Q_{rr} = f(di_F/dt)$
$V_R = 600$ V, $I_F = 40$ A



Typical reverse recovery current as a function of diode current slope

$I_{rrm} = f(di_F/dt)$

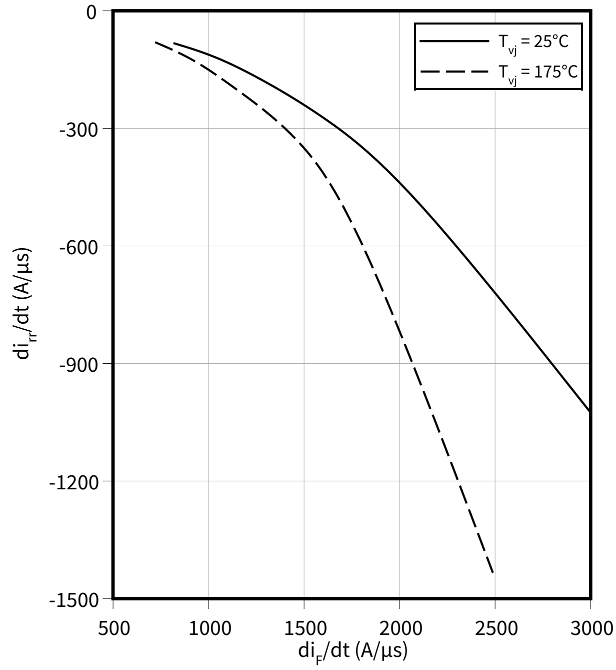
$V_R = 600\ V$, $I_F = 40\ A$



Typical diode peak rate of fall of reverse recovery current as a function of diode current slope

$di_{rr}/dt = f(di_F/dt)$

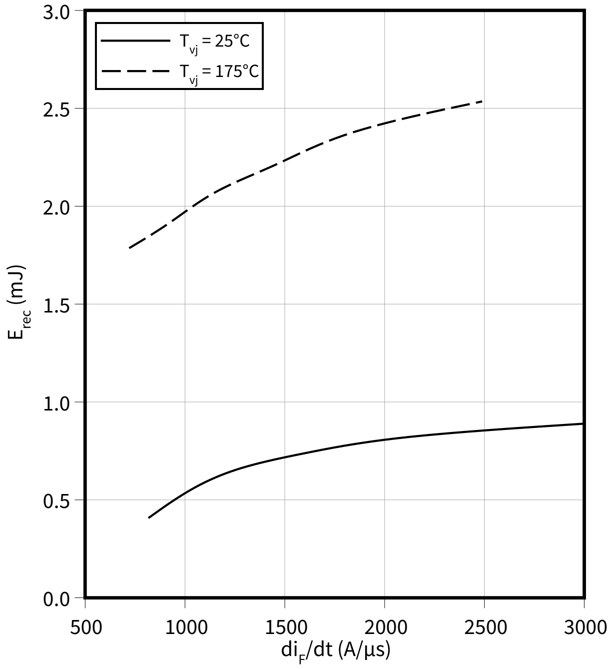
$V_R = 600\ V$, $I_F = 40\ A$



Typical reverse energy losses as a function of diode current slope

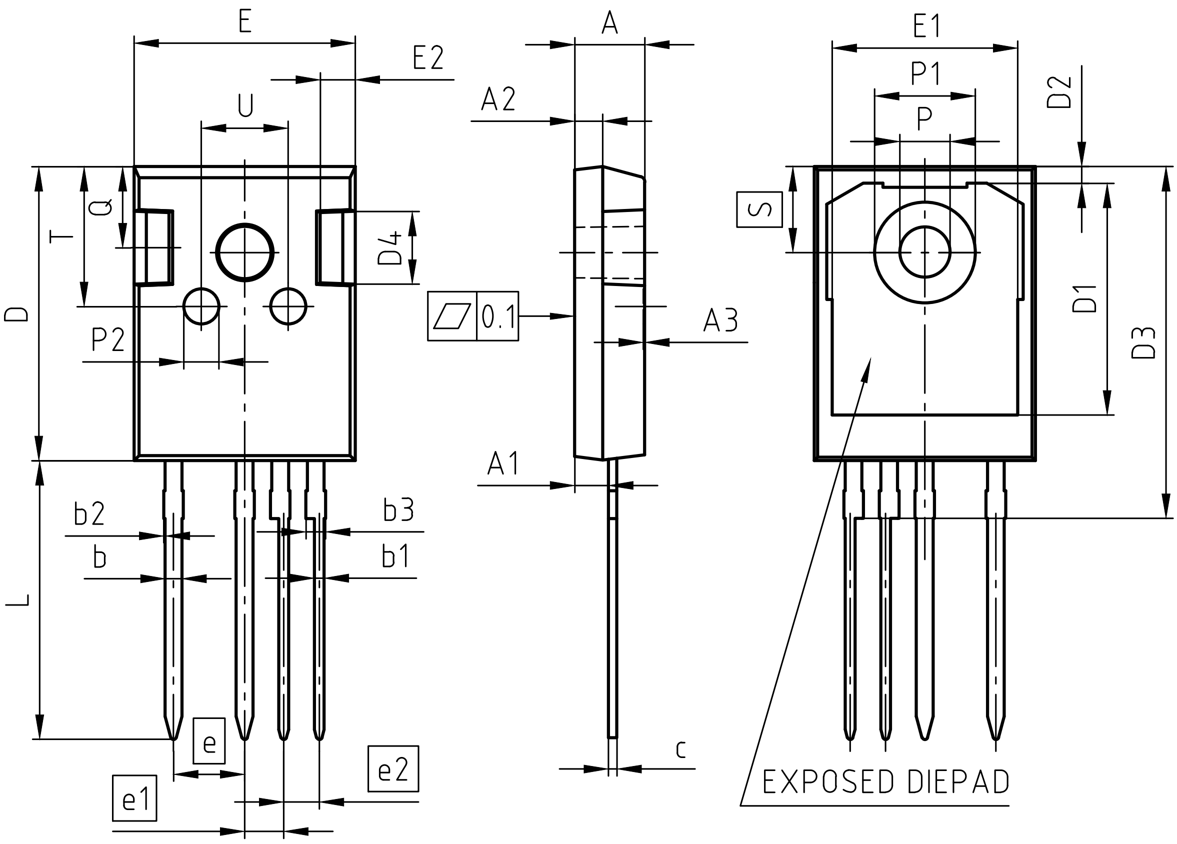
$E_{rec} = f(di_F/dt)$

$V_R = 600\ V$, $I_F = 40\ A$



5 Package outlines

PG-TO247-4-STD-NT3.7



NOTES:
ALL DIMENSIONS DO NOT INCLUDE MOLD FLASH
OR PROTRUSIONS.

PACKAGE - GROUP NUMBER:	PG-TO247-4-U02				
DIMENSIONS	**MILLIMETERS**		**DIMENSIONS**	**MILLIMETERS**	
	MIN.	MAX.		MIN.	MAX.
A	4.90	5.10	**E**	15.70	15.90
A1	2.31	2.51	**E1**	13.10	13.50
A2	1.90	2.10	**E2**	2.40	2.60
A3	0.05	0.25	**e**	5.08	
b	1.10	1.30	**e1**	2.79	
b1	0.65	0.79	**e2**	2.54	
b2	---	0.20	**N**	4	
b3	1.34	1.44	**L**	19.80	20.10
c	0.58	0.66	**øP**	3.50	3.70
D	20.90	21.10	**øP1**	7.00	7.40
D1	16.25	16.85	**øP2**	2.40	2.60
D2	1.05	1.35	**Q**	5.60	6.00
D3	24.97	25.27	**S**	6.15	
D4	4.90	5.10	**T**	9.80	10.20
			U	6.00	6.40

Figure 1

6 Testing conditions

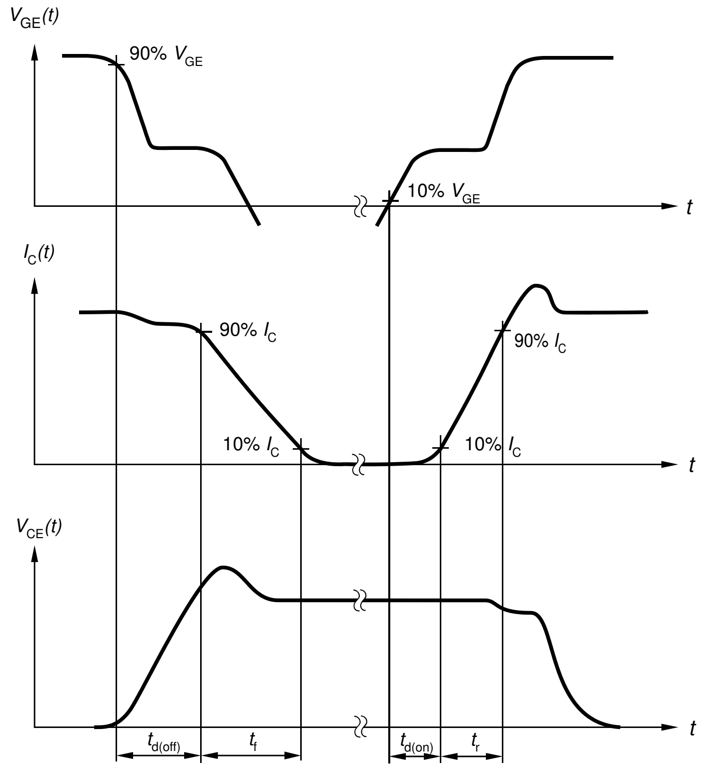


Figure A. **Definition of switching times**

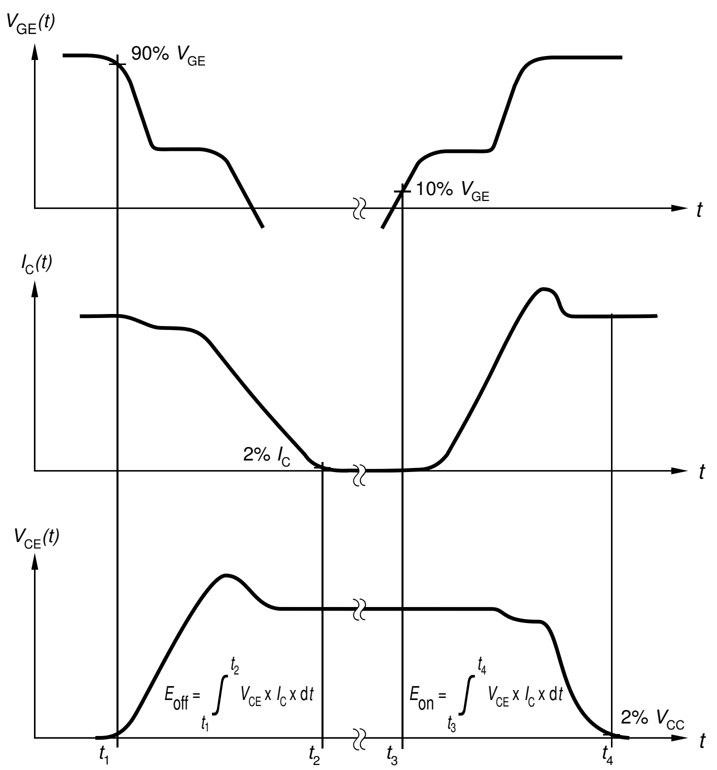


Figure B. **Definition of switching losses**

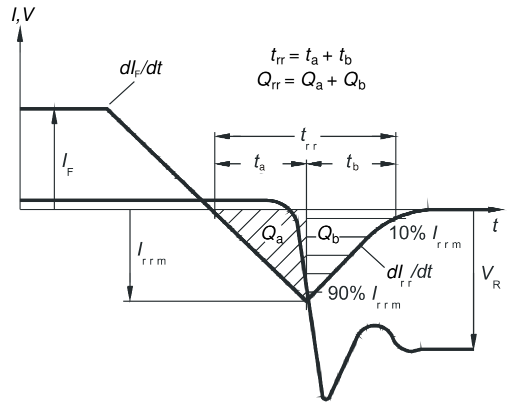


Figure C. **Definition of diode switching characteristics**

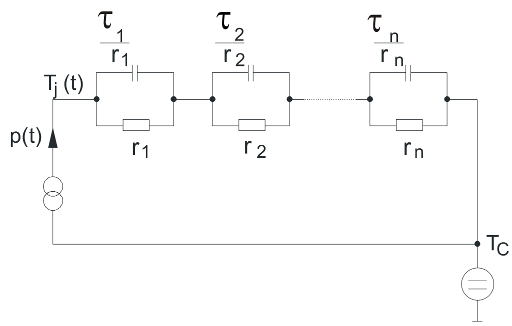


Figure D. **Thermal equivalent circuit**

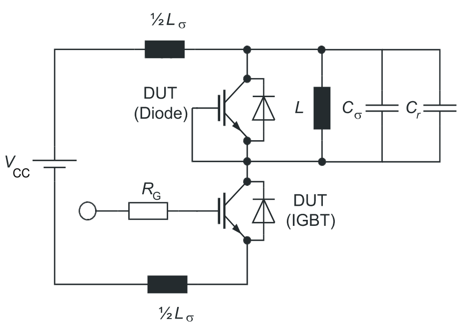


Figure E. **Dynamic test circuit**
Parasitic inductance L_σ,
parasitic capacitor C_σ,
relief capacitor C_r,
(only for ZVT switching)

Figure 2

Revision history

Document revision	Date of release	Description of changes
0.10	2022-05-04	Target datasheet
1.00	2022-12-05	Final datasheet
1.10	2023-01-23	Correction of boundary condition of diagrams $I_{C(SC)}$ = f(V_{GE}) and t_{SC} = f(V_{GE})

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